

precursor in an organic solvent to form a varnish;

(d) coating the varnish on a substrate of a circuit board;

(e) heat curing the varnish, whereupon the reactive groups at the ends cross-link, to form the dielectric film on the substrate.

10. (NEW) The method as recited in claim 9, further comprising the step of:

(f) surface polishing the film.

DI 11. (NEW) The method as recited in claim 10, wherein steps (d), (e) and (f) are repeated to form a multilayer circuit board.

12. (NEW) The method as recited in claim 9, wherein step (e) includes heating at 200°C for thirty minutes, and heating at 350°C for 1-2 hours.

13. (NEW) The method as recited in claim 12, wherein prior to said heating step (e), preheating occurs at 100-120°C for about 10-20 minutes.

14. (NEW) The method as recited in claim 9, wherein either or both of the o-aminophenol compound precursor and aromatic dicarboxylic acid compound precursor is chosen to contain at least one benzene ring substituted by one or more fluorine atoms or trifluoromethyl groups or at least one moiety with one or more trifluoromethyl groups.

15. (NEW) The method as recited in claim 9, wherein the dielectric film is chosen to have a dielectric constant of less than 2.5.

II. REMARKS

A. Rejections in August 7, 2002 Office Action

1. Claims 1-8

Claims 1-8 are rejected as being made obvious by the combination of Murayama et al.